



PATENT  
0020-4652P

IN THE U.S. PATENT AND TRADEMARK OFFICE

# 16/D  
3/12/3  
Surles

Applicant: Narihiro MOROSAWA et al. Conf.: 7107  
Appl. No.: 09/471,173 Group: 2826  
Filed: December 23, 1999 Examiner: K. Quinto  
For: INSULATED GATE TRANSISTOR AND PROCESS  
FOR FABRICATING THE SAME (To be  
Amended)

REPLY UNDER 37 C.F.R. § 1.111

Assistant Commissioner for Patents  
Washington, DC 20231

March 3, 2003  
(Monday)

Sir:

In reply to the Examiner's Office Action dated October 2, 2002, the period for response having been extended two months to March 2, 2003, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE TITLE:

Please amend the title to read: "INSULATED GATE TRANSISTOR HAVING A GATE INSULATOR CONTAINING NITROGEN ATOMS AND FLUORINE ATOMS".

IN THE CLAIMS:

Please amend the following claim:

03/04/2003 JBALINAN 00000147 09471173

01 FC:1252

410.00 OP

RECEIVED  
MAR-5 2003  
TECHNOLOGY CENTER 2800